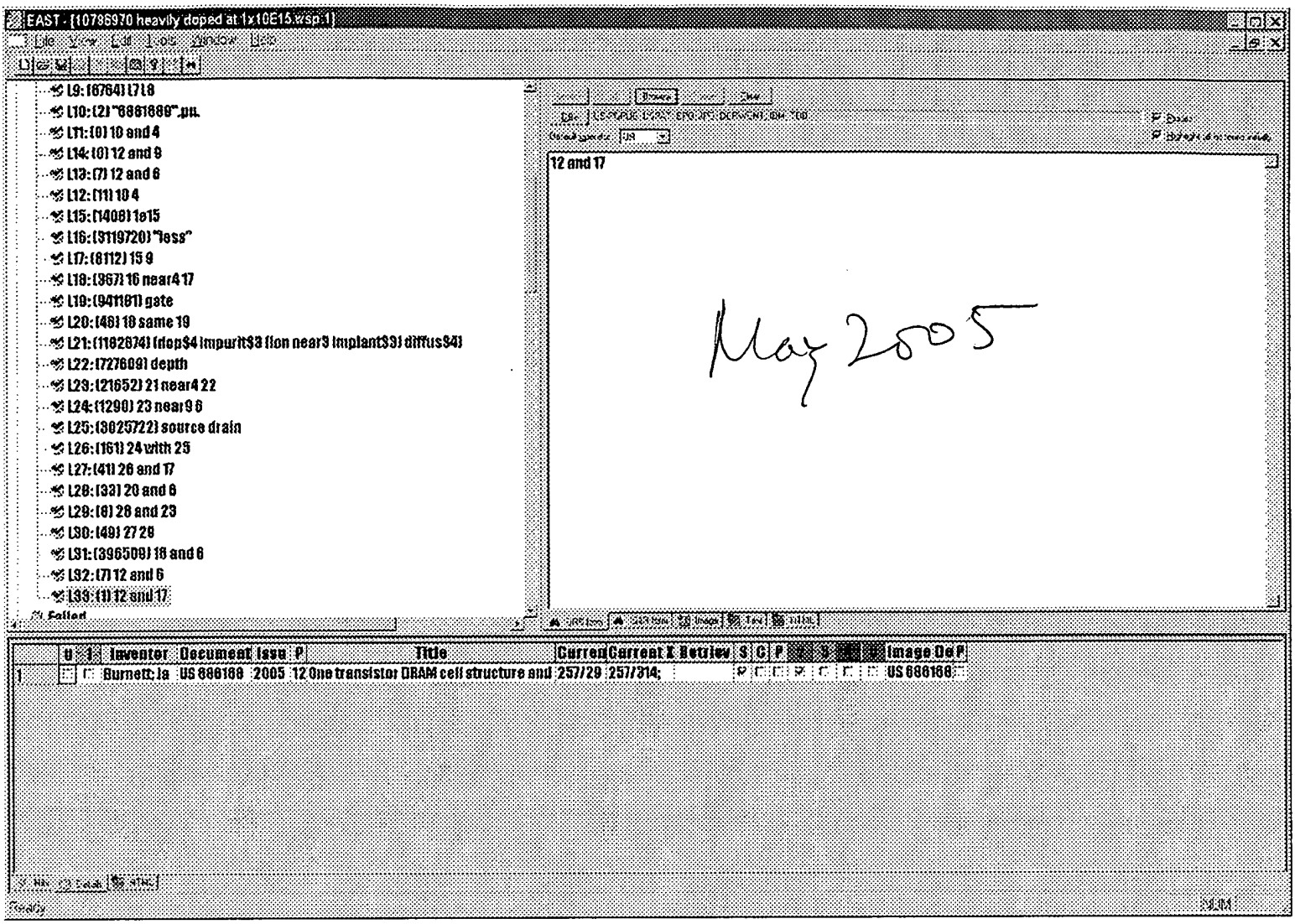
EAST - [10786970 heavily doped at 1x10E15.wsp:1]
File View Edit Tools Window Help
L9: (6764) L7 8
L10: (2) "6861689".pn.
L11: (0) 10 and 4
L14: (0) 12 and 9
L13: (7) 12 and 6
L12: (11) 10 4
L15: (1408) 1e15
L16: (9119720) "loss"
L17: (8112) 15 9
L18: (367) 16 near4 17
L19: (941181) gate
L20: (48) 18 same 19
L21: (11626874) (dop$4 impurit$3 ion near3 implant$3) diffus$4)
L22: (7276091) depth
L23: (21652) 21 near4 22
L24: (1290) 23 near9 6
L25: (3025722) source drain
L26: (161) 24 with 25
L27: (41) 26 and 17
L28: (33) 20 and 6
L29: (6) 28 and 29
L30: (49) 27 29
L31: (396509) 18 and 6
L32: (7) 12 and 6
L33: (1) 12 and 17
Failed
12 and 17
May 2005
U 1 Inventor Document Issue P Title Current Current E Retriev S C P S Image Do P
1 Burnett; Ja US 686168 2005 12 One transistor DRAM cell structure and 257/29 257/314; US 686168
Ready
NUM